



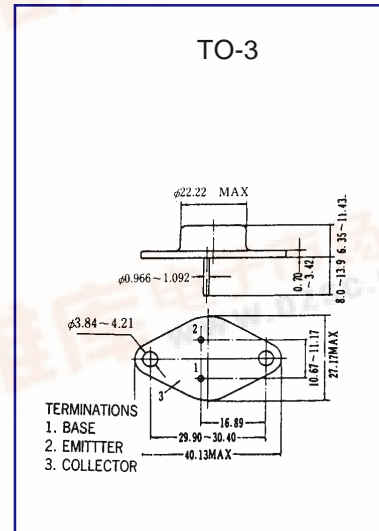
MJ13335

NPN SILICON TRANSISTORS

HIGH VOLTAGE SILICON HIGH POWER TRANSISTORS
SOLENOID AND RELAY DRIVERS

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	800	V
Collector-Emitter Voltage	VCEO	500	V
Collector Current (DC)	IC	20	A
Collector Dissipation (Tc=25°C)	PC	175	W
Junction Temperature	Tj	200	°C
Storage Temperature	Tstg	-50~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB= 800V, IE=0			250	μ A
Collector Cutoff Current	ICEO	VCB= 500V, IB=0			250	μ A
DC Current Gain	hFE	VCE= 5V, IC=5.0A	10			
Collector- Emitter Saturation Voltage	VCE(sat)	IC=10A, IB=2A			1.8	V

